

We Claim:

1. An arc chamber of an ion implanter system comprising:
an arc chamber enclosure for an electron emissive source, said source extending
into said arc chamber enclosure through a wall of said arc chamber enclosure, said wall
through which said source extends comprising an insulator material surrounding said
source.

2. The arc chamber of Claim 1 wherein said insulator material is a high
temperature ceramic material.

3. The arc chamber of Claim 2 wherein said insulator material is
selected from the group consisting of alumina and boron nitride.

4. The arc chamber of Claim 3 wherein said insulator material is boron
nitride.

5. The arc chamber of Claim 1 wherein a substantial portion of said wall
through which said source extends into the arc chamber comprises an insulator material.